

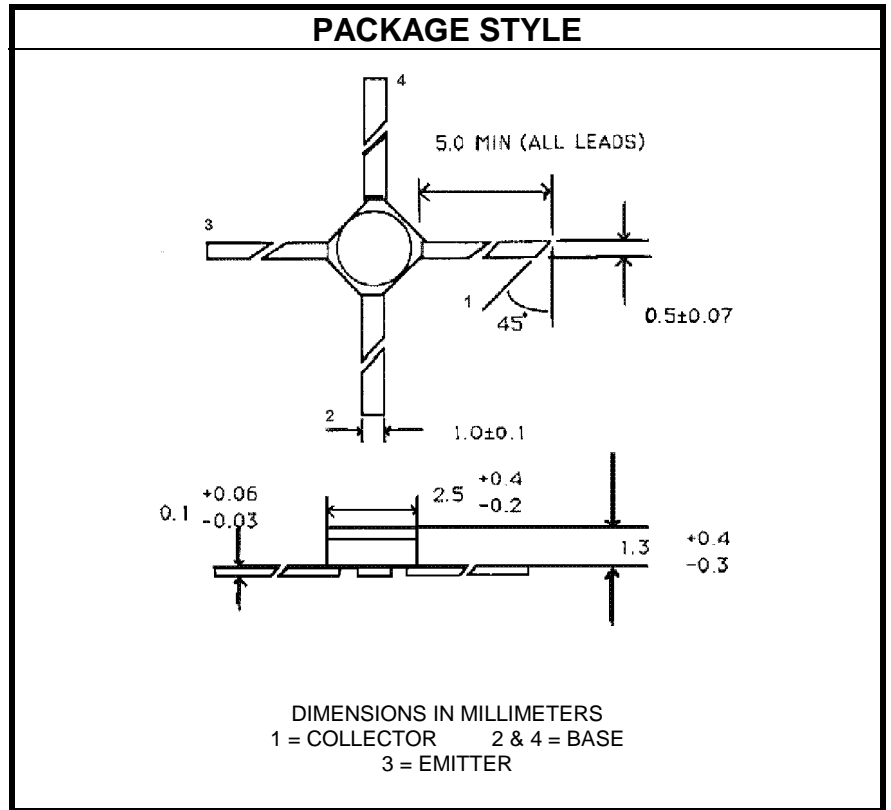
NPN SILICON RF TRANSISTOR

DESCRIPTION:

The **HXTR4101** is a Common Base Device Designed for Oscillator Applications up to 10 GHz.

MAXIMUM RATINGS

I_C	70 mA
V_{EBO}	1.5 V
V_{CEO}	20 V
T_J	300 °C
T_{STG}	-65 °C to 250 °C
P_T	900 mW @ T _C = 25 °C


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I _C = 100 μA			30			V
I_{CEO}	V _{CE} = 15 V					500	μA
I_{CBO}	V _{CB} = 15 V					100	μA
h_{FE}	V _{CE} = 15 V	I _C = 15 mA		50	125	200	---
Posc	V _{CB} = 15 V	I _C = 30 mA	f = 3.0 GHz	19	21.5		dBm
		I _C = 30 mA	f = 4.3 GHz		20.5		
		I _C = 30 mA	f = 6.0 GHz		17		
		I _C = 30 mA	f = 8.0 GHz		12		
N/C	PHASE NOISE TO CARRIER @ 1.0 KHZ FROM THE CARRIER(SSB) f = 4.3 GHz				-50		dBc/Hz